

IN THE SPECIFICATION

Please amend the paragraph beginning at page 8, line 18 as follows:

Figure 7 shows that after completion of diffusion barrier 226, the exemplary method fills at least a portion of the remainder of space 224 (denoted 224' in Figure 6) with one or more insulative materials to form a two-level insulative structure 228. The exemplary embodiment fills substantially all of space 224, which was previously occupied by mask structures 216 and 220, with a single dielectric material using a single procedure. More particularly, the exemplary embodiment vapor deposits a silicon oxide, such as SiO₂, or low-k (that is, low-dielectric-constant) materials, such as xerogels or aerogels. Various methods, such as physical-vapor deposition, chemical-vapor deposition, spin-coating, sol-gel procedures, and so forth can be used to apply these dielectrics.